

# Sputtered Gold as an Effective Schottky Gate for Strained Si/SiGe Nanostructures

G. D. Scott<sup>1,\*</sup>, M. Xiao<sup>1</sup>, E. T. Croke<sup>2</sup>, E. Yablonovitch<sup>3</sup>, and H. W. Jiang<sup>1</sup>

<sup>1</sup>*Department of Physics and Astronomy,  
UCLA, Los Angeles, CA 90095*

<sup>2</sup>*HRL Laboratories, LLC, Malibu, CA 90265*

<sup>3</sup>*Department of Electrical Engineering,  
UCLA, Los Angeles, CA 90095*

(Dated: December 17, 2021)

Metallization of Schottky surface gates by sputtering Au on strained Si/SiGe heterojunctions enables the depletion of the two dimensional electron gas (2DEG) at a relatively small voltage while maintaining an extremely low level of leakage current. A fabrication process has been developed to enable the formation of sub-micron Au electrodes sputtered onto Si/SiGe without the need of a wetting layer.

Significant effort has been directed toward the development of electrostatically defined quantum dots as potential elements for quantum computation information. While a high level of control and sophistication has been achieved in current GaAs/AlGaAs based structures,[1] silicon based heterostructures are expected to have the distinct advantage of possessing extremely long electron phase coherence lifetimes,[2, 3] which can be attributed to the small spin-orbit interaction and the low natural abundance of isotopes with nuclear spin.

Means of control in lateral quantum dot devices is often exercised through the use of Schottky barrier top gates in which metal electrodes patterned on the semiconductor surface capacitively couple to the 2DEG. By applying a bias on the gates one can selectively deplete the charge carriers in the 2DEG directly below, and in the vicinity of, the gates, thereby controlling current flow. Over the last several years attempts were made to create mesoscopic devices on strained Si/SiGe heterostructures by directly mimicking the existing geometries and fabrication processes that have been employed on GaAs/AlGaAs based heterostructures. The success was often limited due to the high level of leakage current and/or the incomplete depletion of the 2DEG by Schottky gates on strained Si/SiGe. Several innovative approaches have recently been introduced as means of circumventing these obstacles.[4, 5, 6] These methods primarily focus on the formation of side gates through various etching techniques. Unfortunately, in order to reach a comparable level of stability, control, and effectiveness of confinement achieved in GaAs based structures, devices using multiple surface gates will most likely be required. Towards this end, both Berer et al.[7] and Slinker et al.[8] have used evaporated Pd on strained Si/SiGe as Schottky gates with positive results. Despite this encouraging development, it is recognized that further improvement of the effectiveness of the Schottky gates is needed to gain control in the few-electron regime.

In this paper, we demonstrate that significant improvements to Schottky gates on Si/SiGe can be made by the proper choice of gate metal and a simple change in the

mechanism of gate metal deposition. In particular, we found that the Schottky gates formed by sputtering Au on strained Si/SiGe heterojunctions enables the depletion of the two dimensional electron gas (2DEG) at a relatively small voltage while maintaining an extremely low level of leakage current.

The devices used for our experiment were fabricated on modulation doped Si/SiGe heterostructures, which are commonly used for the fabrication of lateral quantum dots. These samples have a peak mobility of about  $10^5 \text{ cm}^2/\text{V} - \text{sec}$  at a density of  $3 \times 10^{11}/\text{cm}^2$ , and are grown by MBE with a layer by layer composition as follows: Si(5nm)/SiGe<sub>0.25</sub>(35nm)/ $\delta$ -dopedSb =  $2 \times 10^{12} \text{ cm}^{-2}$ /SiGe<sub>0.25</sub>(22.5nm)/Si(15nm)/SiGe<sub>0.25</sub>(1 $\mu\text{m}$ )/SiGe<sub>0.20-0.25</sub>(0.9 $\mu\text{m}$ )/SiGe<sub>0.108-0.20</sub>(1.5 $\mu\text{m}$ )/SiGe<sub>0.018-0.108</sub>(1.5 $\mu\text{m}$ )/Si(100nm)/ p-Si(100) substrate.

To test the effectiveness of various Schottky gates, a large square gate (150 $\mu\text{m} \times 150\mu\text{m}$ ) was defined by UV lithography atop a chemically etched mesa. Ohmic contacts to the 2DEG were formed by phosphors ion implantation. Pd, Cr and Au films were deposited as gate metals by evaporation. The coupling strength between the gate and 2DEG (i.e. depletion voltage) as well as leakage between the gate and 2DEG were both measured as a function of applied voltage (Fig 1). The results of the leakage current from the evaporated gates are in line with the known Schottky barrier values. For Pd the onset of measurable leakage began at a larger value of applied bias, in accordance with the larger Schottky barrier it forms with n-type silicon. However, in terms of effectiveness of gate-coupling, Pd required a correspondingly larger value of bias to fully deplete the 2DEG. The strongest coupling between gate and 2DEG was found with Au, which required only a very small voltage for the complete depletion of the 2DEG, but had unacceptably high levels of leakage current.

The Schottky-Mott theory predicts that the Schottky barrier height,  $\Phi_B$ , will depend linearly on the metal work function  $\Phi_B = (\Phi_m - \chi_s)$ , where  $\Phi_m$  is the work function of the metal and  $\chi_s$  is the electron affinity of the semiconductor. This relation does not always hold in

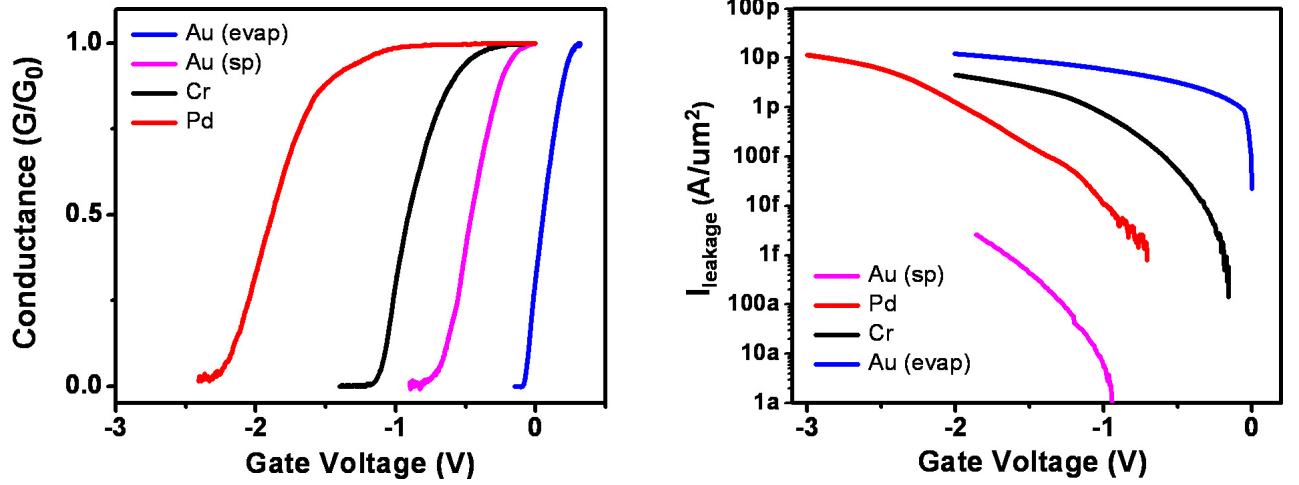


FIG. 1: a) Conductance measured as a function of applied gate voltage for four different gate compositions. b) Leakage current per square micron of gate electrode measured as a function of applied voltage for the same four samples. Gates of sputtered Au demonstrate levels of leakage several orders of magnitude lower, on average, and possess strong coupling to the 2DEG.

practice. When a metal and a semiconductor are joined together,  $\Phi_B$  will depend sensitively not only on the identity of the materials, but also on the details of the interface structure that results. In covalently bonded semiconductors, such as silicon, surface gates may be unable to effectively modulate the density of the underlying 2DEG due to localized surface charges. The large values of applied voltage necessary to cause depletion with Pd and Cr gates are indicative of correspondingly large surface charge densities.

The choice of gate metal will influence the relative magnitude of  $\Phi_B$ , and a larger  $\Phi_B$  dictates a lower level of leakage current from the metal to the semiconductor at a particular bias. But even though Pd, for example, has a relatively large  $\Phi_B$ , a large voltage is also required to achieve depletion. Higher operating biases lead to increased levels of leakage current, which in turn compromise the surface gate characteristics.

We also deposited gold by sputtering instead of evaporation. Gates with a sputtered layer of gold always demonstrated dramatically less leakage current as compared to the evaporated gates, while maintaining excellent coupling to the 2DEG (Fig 1). The kinetic energy of evaporated atoms corresponds to the temperature of the evaporating surface, and is therefore typically around 0.1 - 0.3 eV. The energy of sputtered atoms is roughly 100 times greater (for Au:  $\sim 8$ -16 eV).[9, 10, 11] According to the software program “Stopping and Range of Ions in Matter” (SRIM), sputtered gold atoms may penetrate into silicon to a depth of around 1 nm, while evaporated atoms will not penetrate at all. The ability of sputtered gold atoms to penetrate the silicon cap will promote an interdiffusion of gold and silicon, possibly triggering the formation of gold silicide compounds.[12, 13] We speculate that, much akin to platinum silicide,[14] gold silicide may form a larger, more stable Schottky barrier with n-

type silicon when compared to bare gold.

Unfortunately, thin films of Au will not customarily adhere well to silicon due to the  $\text{SiO}_2$  that forms on the surface, causing serious problems during the liftoff phase of the fabrication procedure. By removing the native oxide layer with a buffered oxide etch ( $\text{NH}_3\text{F}:\text{HF}$ , 6:1), we found it possible to attain sufficient adhesion enabling us to repeatedly and reproducibly form devices out of evaporated and sputtered Au without any liftoff problems.

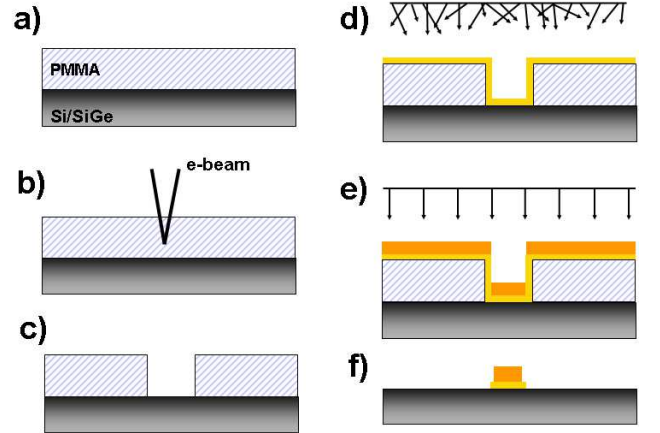


FIG. 2: Fabrication Steps. a) The substrate is spin-coated with 495 PMMA. b) Electron beam lithography is used to define the device pattern. c) PMMA exposed during the Ebeam writing process is removed after developing. The sample is then placed in a BOE solution for 15 seconds to remove  $\text{SiO}_2$  layer. d) A thin layer of gold is sputtered onto the surface. To allow for liftoff, the sputtered layer must be kept to a minimum thickness. e) A thicker layer of gold is evaporated on top of the sputtered gold layer. f) Liftoff in hot acetone leaves an intact device with excellent leakage properties.

Unlike the deposition of metal by evaporation, during

the sputtering process metal is not deposited from one direction (Fig 2d). As Argon ions bombard the sputtering target, gold atoms are deposited from many different directions. The result is that sputtering may generate complete coverage of the developed lithography pattern, making liftoff extremely difficult, if not impossible. This is especially problematic for thinner resists and finer lithographic structures, namely for electron beam lithography using PMMA resist. Since the majority of nanoscale devices necessitate the use of electron beam lithography, a fabrication technique was required that would facilitate metallization by sputtering.

We found that if the sputtered layer is thin enough ( $\lesssim 15$  nm) it can still be lifted off cleanly. The final devices were produced by using a BOE to remove the  $\text{SiO}_2$  immediately prior to metallization. We then sputter a thin layer (12 nm) of gold onto the surface. After sputtering, a thicker layer of gold (35 nm) is deposited by electron beam evaporation to reinforce the structural integrity of the device. Lift off was then performed in heated acetone (55 C) for approximately 2 hours (Fig 2).

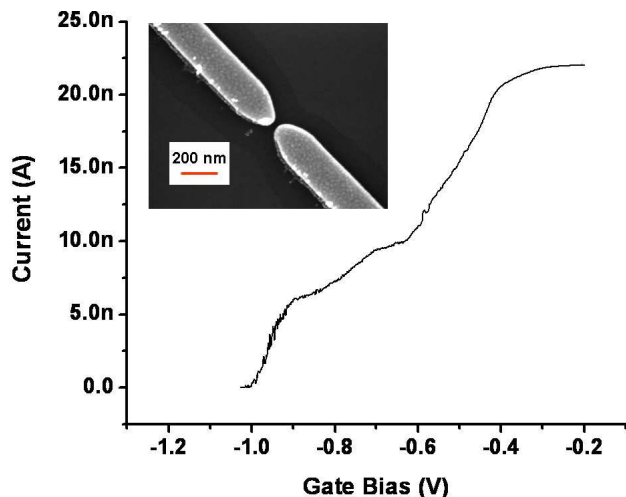


FIG. 3: Current through a split gate, fabricated with a sputtered layer of gold, as a function of applied voltage. Stepwise depopulation of edge channels as evinced through decreasing steps in current, as well as a pinch off voltage around -1.0 V indicate excellent gate characteristics. Inset: SEM picture of the split gate structure.

Complete pinch off of the current through split gate structures in devices formed by this fabrication technique (Fig 3 inset) was observed to occur at biases in accordance with Fig 1a, indicating a strong coupling between the gate electrodes and the 2DEG. The emergence of more pronounced steps in the depletion curves, demonstrating the stepwise depopulation of available edge channels, is evidence of sharp electrostatic confinement beneath the gates. Both the lower operating bias necessary to achieve depletion, and the enormous reduction of leakage current lead to a more stable electrostatic environment, which will be necessary for developing the next

generation of SiGe based devices.

By using Schottky surface gates formed with sputtered Au, we demonstrated that it is possible to dramatically reduce the leakage current in strained Si/SiGe while simultaneously improving the coupling strength between the gates and 2DEG. The advantages of sputtering, as opposed to thermal or electron beam evaporation, are likely due to the interdiffusion of Au and Si leading to the formation of gold-silicide compounds. A nano-fabrication process is developed specifically to enable the fabrication of Au sputtered sub-micron gates. A split gate device using this technique demonstrates excellent electrostatic characteristics. Advancements in the effectiveness of Schottky gates allows for the continued use of conventional surface gate geometries, superseding the need for more exotic gating techniques.

The authors would like to thank Thomas Szkopek for many insightful discussions. This work is supported by the Defense MicroElectronics Activity (DMEA 90-02-2-0217) and by MARCO MSD Center.

---

\* Electronic address: gscott@physics.ucla.edu

- [1] see for example, J. M. Elzerman et al., *Nature*, **430**, 431 (2005), and J. R. Petta et al., *Science* **309**, 2180 (2005).
- [2] R. Vrijen, E. Yablonovitch, K. Wang, H. W. Jiang, A. Balandin, V. Roychowdhury, and T. Mor, *Phys. Rev. A*, **62**, 012306 (2000).
- [3] A. M. Tyryshkin, S. A. Lyon, A. V. Astashkin, and A. M. Raitsimring, *Phys. Rev. B*, **68**, 193207 (2003).
- [4] X. Z. Bo, L. P. Rokhinson, H. Yin, D. C. Tsui, and J. C. Sturm, *Appl. Phys. Lett.*, **81**, 3263 (2002).
- [5] L. J. Klein, K. A. Slinker, J. L. Truitt, S. Goswami, K. L. M. Lewish, S. N. Coppersmith, D. W. van der Weide, M. Friesen, R. H. Blick, D. E. Savage, M. G. Lagally, C. Tahan, R. Joynt, M. A. Eriksson, J. O. Chu, J. A. Ott, and P. M. Mooney, *Appl. Phys. Lett.*, **84**, 4047 (2004).
- [6] M. R. Sakr, E. Yablonovitch, E. T. Croke, and H. W. Jiang, *Appl. Phys. Lett.*, **87**, 223104 (2005).
- [7] T. Berer, D. Pachinger, G. Pillwein, M. Muhlberger, H. Lichtenberger, G. Brunthaler, and F. Schaffler, *arXiv:cond-mat/0508260* (2005).
- [8] K. A. Slinker, K. L. M. Lewis, C. C. Haselby, S. Goswami, L. J. Klein, J. O. Chu, S. N. Coppersmith, R. Joynt, R. H. Blick, M. Friesen, and M. A. Eriksson, *arXiv/0508107* (2005).
- [9] G. K. Wehner, *Phys. Rev.*, **114**, 1270 (1959).
- [10] G. M. Turner, I. S. Falconer, B. W. James, and D. R. McKenzie, *J. Vac. Sci. Technol.*, **10**, 455 (1992).
- [11] B. Satpati, P. V. Satyam, T. Som, and B. N. Dev, *arXiv:cond-mat/503030* (1992).
- [12] V. G. Zavodinsky and I. A. Kuyanov, *J. Appl. Phys.* **81**, 6 (1997).
- [13] B. L. Sharma, *Metal-Semiconductor Schottky Barrier Junction and Their Applications*, 113 (Plenum Press, New York, 1984).
- [14] B. G. Streetman and S. K. Banerjee, *Solid State Electronic Devices*, (Prentice Hall, Englewood Cliffs, NJ 1980).